KSB1116(A)

Rev.E Mar.-2016

DATA SHEET

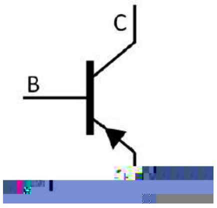
WR0<5 ṂṂ Ŀ SQS Æ Ṁ ɥ s Ⅱ ↿ Silicon PNP transistor in a TO-92 Plastic Package.

љ NVG4949+D, Ӎ ´

Complementary pair with KSD1616(A).

[illegible]

Audio frequency power amplifier, medium speed switching.

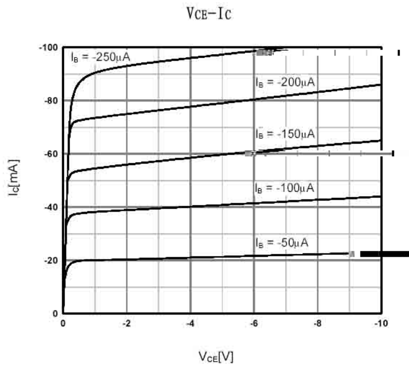


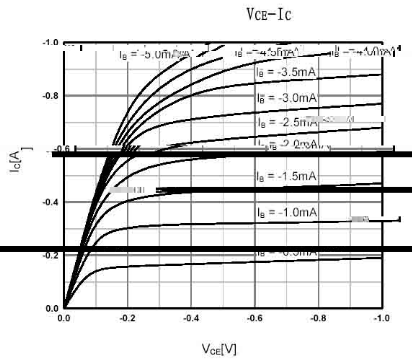
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

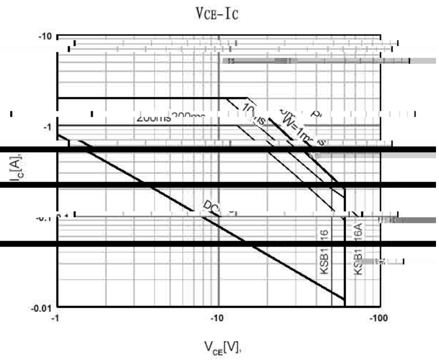
ν ῼ Parameter	Ɏ ᴺ Symbol		ῼ Ѳ Rating	ᴅ ɏ Unit
Collector to Base Voltage	V_{CBO}	KSB1116	-60	V
		KSB1116A	-120	
Collector to Emitter Voltage	V_{CEO}	KSB1116	-50	V
		KSB1116A	-60	
Emitter to Base Voltage	V_{EBO}		-6.0	V
Collector Current - Continuous	I_C		-1.0	A
Base Current – Continuous	I_B		-2.0	A
Collector Power Dissipation	P_C		750	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T_{stg}		-55 150	

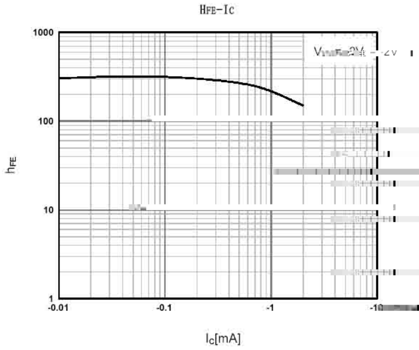
ν ῼ Parameter	Ɏ ᴺ Symbol	╜ ⁏ ↑ ƫ Test Conditions	ῳ ṇ Ѳ Min	Ɛ ʒ Ѳ Typ	ῳ ⁿ Ѳ Max	ᴅ ɏ Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=-60V I_E=0			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-6.0V I_C=0			-0.1	μA
DC Current Gain	$h_{FE(1)}$ KSB1116	V_{CE}=-2.0V I_C=-100mA	135		600	

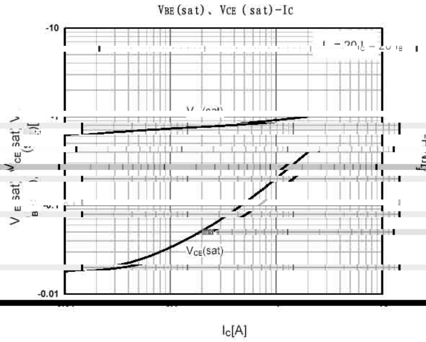
/ Electrical Characteristic Curve

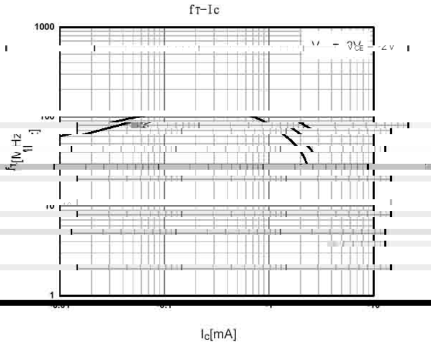


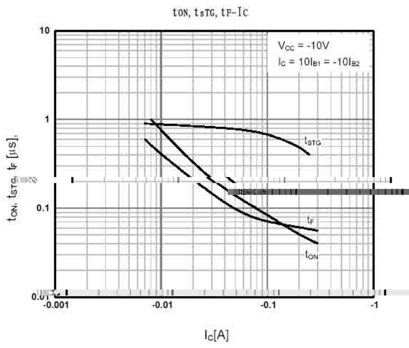


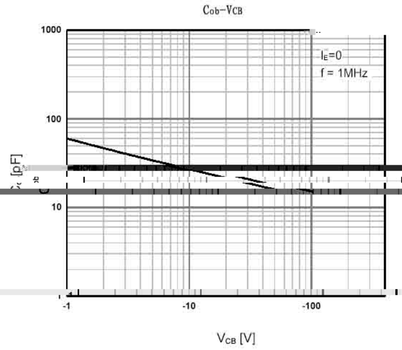


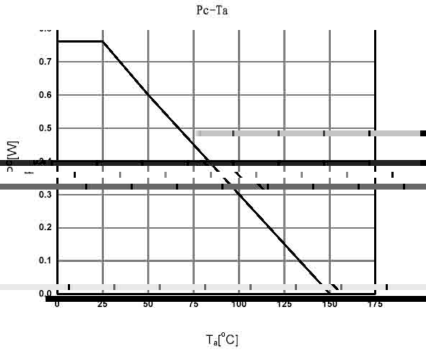




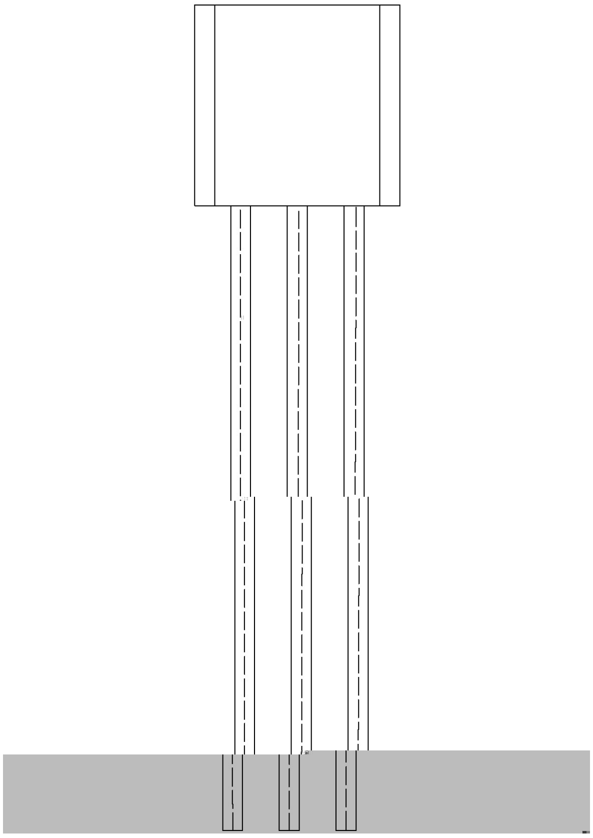








/ Marking Instructions



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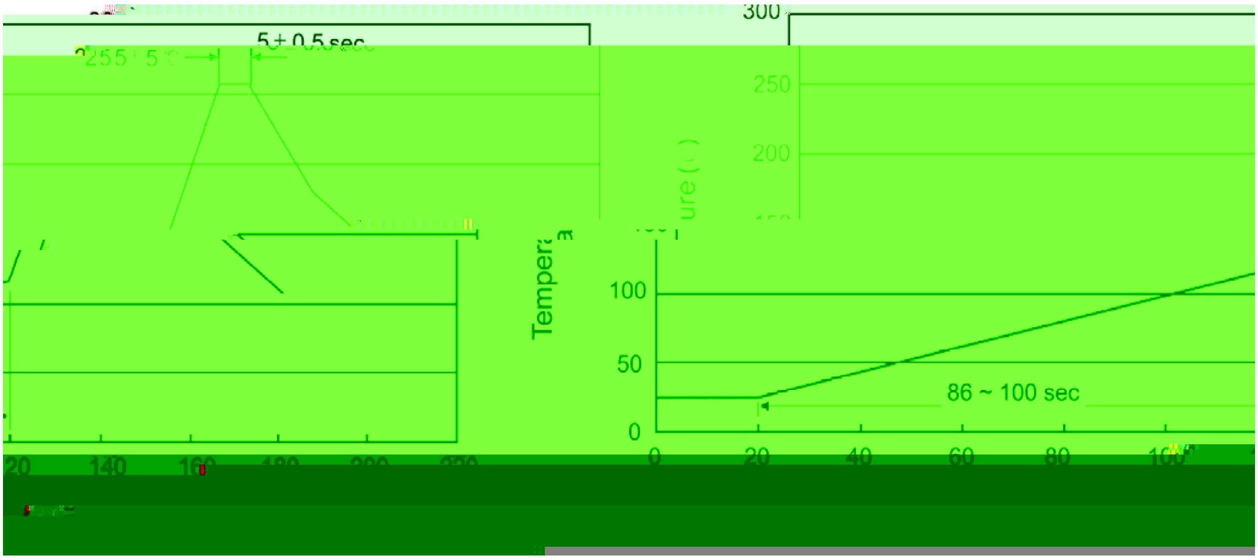
E4449 χ	ѭ ȝ ᴺ Ꮒ

(　　) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ
1　ſ ♬ □ ŷ 25 Ḱ 150 ł　ı `H ɉ 60 Ḱ 90sec;
2　Š Ӫ □ ŷ 255 ° 5 ł　ı `H ɉ `Y 𐑍 ㎃ 5 ° 0.5sec;
3　ì ˙　Ⅰ ˛　ɔ ङ ŷ ㎃ 2 Ḱ 10 ł /sec.

Note:
1.Preheating:25~150 ł , Time:60~90sec.
2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.
3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ŷ χ 270 ° 5 ł　　`H ɉ χ 10 ° 1 sec.　　Temp:270±5　　Time:10±1 sec

/ Packaging SPEC.

῟Ω ʈ γ ŀ　/　BULK

Package Type	Units	Dimension 314	0